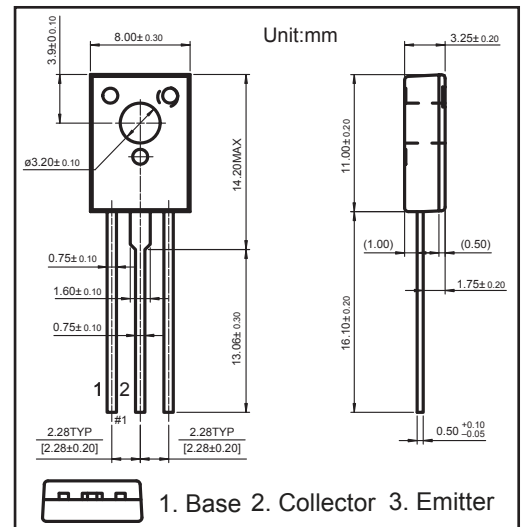


TO-18 Plastic-Encapsulate Transistors
FEATURES

- Low Frequency Power Amplifier
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-18 molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	35	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	2.5	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 1mA, I_E = 0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 1mA, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 35V, I_E = 0$			20	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			20	μA
DC current gain	h_{FE1}	$V_{CE} = 2V, I_C = 0.5A$	60		320	
	h_{FE2}	$V_{CE} = 2V, I_C = 1.5A$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 200mA$			1	V
Base-collector voltage	V_{BE}	$V_{CE} = 2V, I_C = 1.5A$			1.5	V
Transition frequency	f_T	$V_{CE} = 2V, I_C = 200mA$		180		MHz